



High Common-Mode Voltage Difference Amplifier

FEATURES

Common-Mode Voltage Range: ±275 V

Minimum CMRR: 90 dB from -40°C to +125°C

• DC Specifications:

- Maximum Offset Voltage: 1100 μV

Maximum Offset Voltage Drift: 15 μV/°C

Maximum Gain Error: 0.02%

Maximum Gain Error Drift: 10 ppm/°C

Maximum Gain Nonlinearity: 0.001% FSR

AC Performance:

Bandwidth: 500 kHz

Typical Slew Rate: 5 V/µs

Wide Supply Range: ±2.0 V to ±18 V

- Maximum Quiescent Current: 900 μA

Output Swing on ±15-V Supplies: ±13.5 V

Input Protection:

Common-Mode: ±500 V

Differential: ±500 V

APPLICATIONS

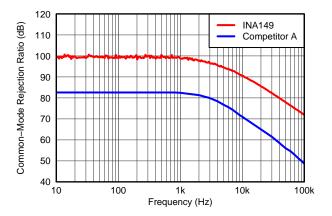
- High-Voltage Current Sensing
- Battery Cell Voltage Monitoring
- Power-Supply Current Monitoring
- Motor Controls
- Replacement for Isolation Circuits

DESCRIPTION

The INA149 is a precision unity-gain difference amplifier with a very high input common-mode voltage range. It is a single, monolithic device that consists of a precision op amp and an integrated thinfilm resistor network. The INA149 can accurately measure small differential voltages in the presence of common-mode signals up to ±275 V. The INA149 inputs are protected from momentary common-mode or differential overloads of up to 500 V.

In many applications, where galvanic isolation in not required, the INA149 can replace isolation amplifiers. This ability can eliminate costly isolated input side power supplies and the associated ripple, noise, and quiescent current. The excellent 0.0005% nonlinearity and 500-kHz bandwidth of the INA149 are superior to those of conventional isolation amplifiers.

The INA149 is pin-compatible with the INA117 and INA148 type high common-mode voltage amplifiers and offers improved performance over both devices. The INA149 is available in the SOIC-8 package with operation specified over the extended industrial temperature range of –40°C to +125°C.







This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

PACKAGE/ORDERING INFORMATION(1)

PRODUCT	PRODUCT PACKAGE-LEAD		PACKAGE MARKING		
INA149	SOIC-8	D	INA149A		

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

ABSOLUTE MAXIMUM RATINGS(1)

Over operating free-air temperature range, unless otherwise noted.

		INA149	UNIT	
Supply voltage	(V+) - (V-)	40	V	
Input voltage range	Continuous	300	V	
Common-mode and differential, 10) s	500	V	
Maximum Voltage on REF _A and R	EF _B	(V-) - 0.3 to (V+) + 0.3	V	
Input current on any input pin (2)		10 mA		
Output short-circuit current duratio	n	Indefinite		
Operating temperature range		-55 to +150	°C	
Storage temperature range		-65 to +150	°C	
Junction temperature		+150	°C	
	Human body model (HBM)	1500	V	
ESD rating	Charged device model (CDM)	1000	V	
	Machine model (MM)	100	V	

⁽¹⁾ Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

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⁽²⁾ REF_A and REF_B are diode clamped to the power-supply rails. Signals applied to these pins that can swing more than 0.3 V beyond the supply rails should be limited to 10 mA or less.

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ELECTRICAL CHARACTERISTICS: V+ = +15 V and V- = -15 V

At T_A = +25°C, R_L = 2 k Ω connected to ground, and V_{CM} = REF_A = REF_B = GND, unless otherwise noted.

		INA149 MIN TYP MAX			
PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT	
GAIN				"	
Initial	V _{OUT} = ±10.0 V		1		V/V
Gain error	V _{OUT} = ±10.0 V		±0.005	±0.02	%FSR
Gain	vs temperature, $T_A = -40^{\circ}\text{C}$ to +125°C		±1.5	±10	ppm/°C
Nonlinearity			±0.0005	±0.001	%FSR
OFFSET VOLTAGE					
			350	1100	μV
Initial offset	vs temperature, $T_A = -40^{\circ}\text{C}$ to +125°C		3	15	μV/°C
	vs supply (PSRR), V _S = ±2 V to ±18 V	90	120		dB
INPUT				'	
	Differential		800		kΩ
Impedance	Common-mode		200		kΩ
	Differential	-13.5		13.5	V
Voltage range	Common-mode	-275		275	V
	At dc, V _{CM} = ±275 V	90	100		dB
Common-mode rejection	vs temperature, $T_A = -40^{\circ}\text{C}$ to +125°C, at dc	90			dB
(CMRR)	At ac, 500 Hz, V _{CM} = 500 V _{PP}	90			dB
	At ac, 1 kHz, V _{CM} = 500 V _{PP}		90		dB
OUTPUT				<u> </u>	
Voltage range		-13.5		13.5	V
Short-circuit current			±25		mA
Capacitive load drive	No sustained oscillations		10		nF
OUTPUT NOISE VOLTAGE				'	
0.01 Hz to 10 Hz			20		μV_{PP}
10 kHz			550		nV/√ Hz
DYNAMIC RESPONSE				*	
Small-signal bandwidth			500		kHz
Slew rate	$V_{OUT} = \pm 10$ -V step	1.7	5		V/µs
Full-power bandwidth	$V_{OUT} = 20 V_{PP}$		32		kHz
Settling time	0.01%, V _{OUT} = 10-V step		7		μs
POWER SUPPLY				"	
Voltage range		±2		±18	V
	$V_S = \pm 18 \text{ V}, V_{OUT} = 0 \text{ V}$		810	900	μA
Quiescent current	vs temperature, $T_A = -40^{\circ}\text{C}$ to +125°C			1.1	mA
TEMPERATURE RANGE		1		· L	
Specified		-40		+125	°C
Operating		-55		+150	°C
Storage		-65		+150	°C



ELECTRICAL CHARACTERISTICS: V+ = 5 V and V- = 0 V

At T_A = +25°C, R_L = 2 k Ω connected to 2.5 V, and V_{CM} = REF_A = REF_B = 2.5 V, unless otherwise noted.

		INA149		
PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
GAIN			•	
Initial	V _{OUT} = 1.5 V to 3.5 V	1		V/V
Gain error	V _{OUT} = 1.5 V to 3.5 V	±0.005		%FSR
Gain				ppm/°C
Nonlinearity		±0.0005		%FSR
OFFSET VOLTAGE				
		350		μV
Initial offset	vs temperature, T _A = -40°C to +125°C	3		μV/°C
	vs supply (PSRR), $V_S = 4 \text{ V to 5 V}$	120		dB
INPUT	-		<u> </u>	
	Differential	800		kΩ
Impedance	Common-mode	200		kΩ
	Differential	1.5	3.5	V
Voltage range	Common-mode	-20	25	V
	At dc, $V_{CM} = -20 \text{ V to } 25 \text{ V}$	100		dB
	vs temperature, $T_A = -40^{\circ}\text{C}$ to +125°C, at dc	100		dB
Common-mode rejection	At ac, 500 Hz, V _{CM} = 49 V _{PP}	100		dB
	At ac, 1 kHz, V _{CM} = 49 V _{PP}	90		dB
OUTPUT				
Voltage range		1.5	3.5	V
Short-circuit current		±15		mA
Capacitive load drive	No sustained oscillations	10		nF
OUTPUT NOISE VOLTAGE	1			
0.01 Hz to 10 Hz		20		μV _{PP}
10 kHz		550		nV/√ Hz
DYNAMIC RESPONSE				
Small-signal bandwidth		500		kHz
Slew rate	V _{OUT} = 2 V _{PP} step	5		V/µs
Full-power bandwidth	V _{OUT} = 2 V _{PP}	32		kHz
Settling time	0.01%, V _{OUT} = 2 V _{PP} step	7		μs
POWER SUPPLY	. 551 11 1			
Voltage range		5		V
	V _S = 5 V	810		μA
Quiescent current	vs temperature, T _A = -40°C to +125°C	1		mA

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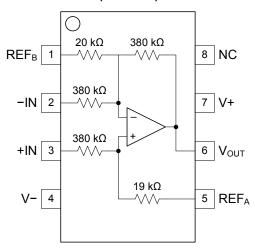
THERMAL INFORMATION

		INA149		
	THERMAL METRIC ⁽¹⁾	D (SOIC)	UNITS	
		8 PINS		
θ_{JA}	Junction-to-ambient thermal resistance	110		
θ_{JCtop}	Junction-to-case (top) thermal resistance	57		
θ_{JB}	Junction-to-board thermal resistance	54	°C/W	
ΨЈТ	Junction-to-top characterization parameter	11	C/VV	
ΨЈВ	Junction-to-board characterization parameter	53		
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	N/A		

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

PIN CONFIGURATION

D PACKAGE SOIC-8 (TOP VIEW)



PIN DESCRIPTIONS

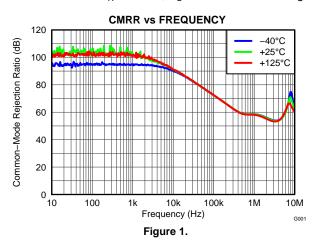
NAME	NO.	DESCRIPTION				
–IN	2	Inverting input				
+IN	3	Noninverting input				
NC	8	No internal connection				
REFA	5	Reference input				
REF _B	1	Reference input				
V-	4	Negative power supply				
V+	7	Positive power supply ⁽¹⁾				
V _{OUT}	6	Output				

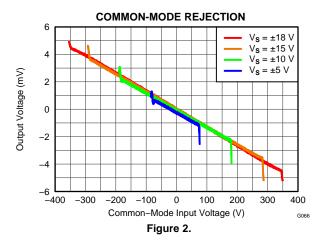
(1) In this document, (V+) – (V–) is referred to as V_S .

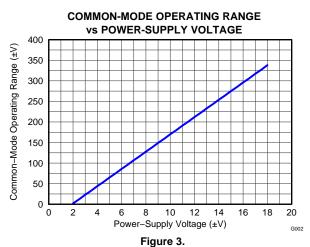


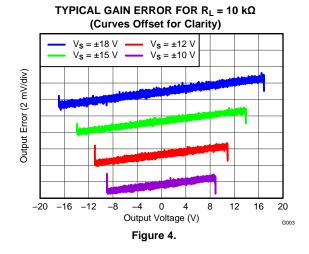
TYPICAL CHARACTERISTICS

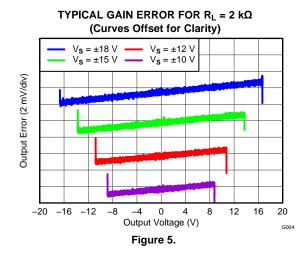
At $T_A = +25$ °C, $R_L = 2 \text{ k}\Omega$ connected to ground, and $V_S = \pm 15 \text{ V}$, unless otherwise noted.

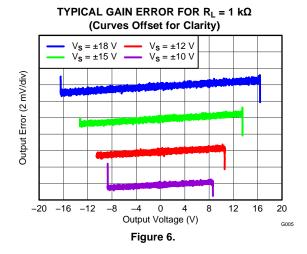














At T_A = +25°C, R_L = 2 k Ω connected to ground, and V_S = ±15 V, unless otherwise noted.

TYPICAL GAIN ERROR FOR LOW SUPPLY VOLTAGES (Curves Offset for Clarity)

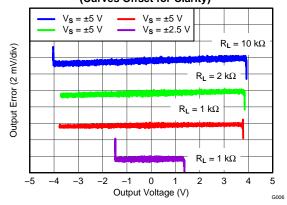


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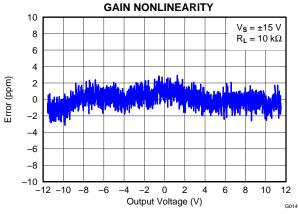


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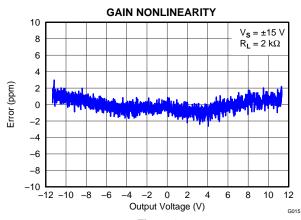


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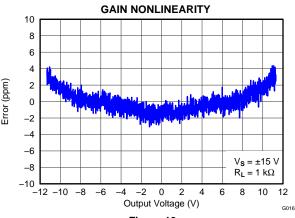


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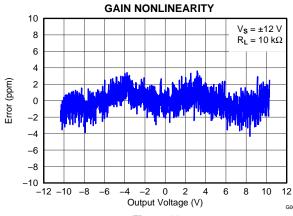


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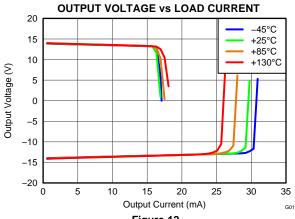


Figure 12.



At $T_A = +25$ °C, $R_L = 2 \text{ k}\Omega$ connected to ground, and $V_S = \pm 15 \text{ V}$, unless otherwise noted.

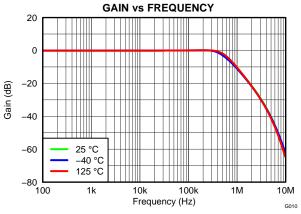


Figure 13.

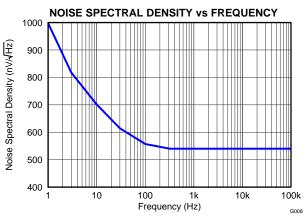


Figure 14.

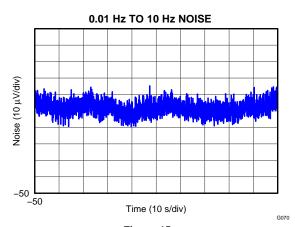
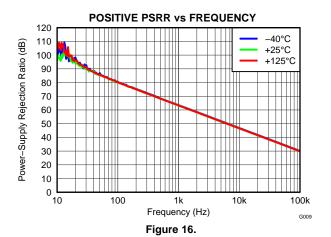
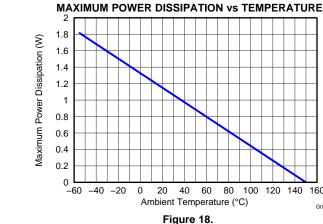
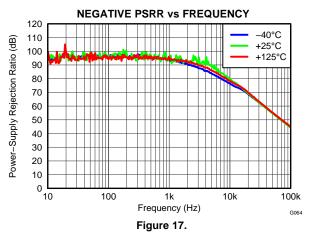


Figure 15.





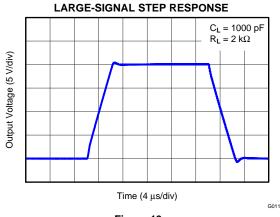


60 _60 _40 _20 20 40 80 100 120 140 0 160 Ambient Temperature (°C)

Figure 18.



At T_A = +25°C, R_L = 2 k Ω connected to ground, and V_S = ±15 V, unless otherwise noted.



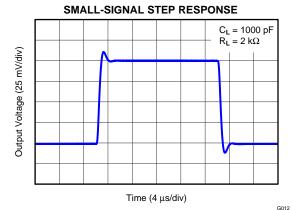
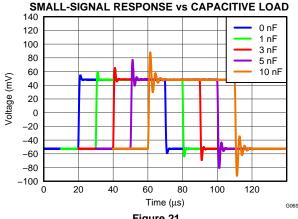


Figure 19.

Figure 20.



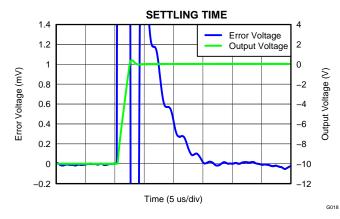
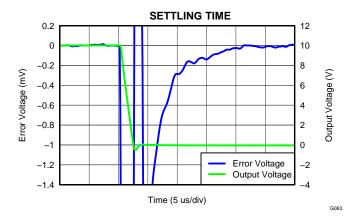


Figure 21.

Figure 22.



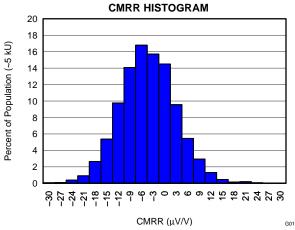
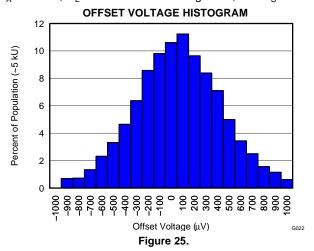


Figure 23.

Figure 24.



At $T_A = +25$ °C, $R_L = 2 \text{ k}\Omega$ connected to ground, and $V_S = \pm 15 \text{ V}$, unless otherwise noted.



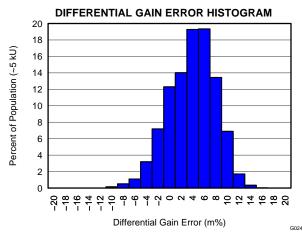
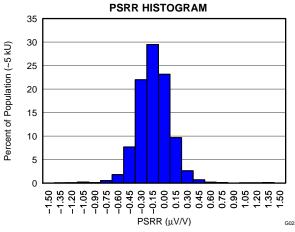


Figure 26.



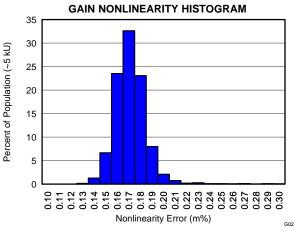
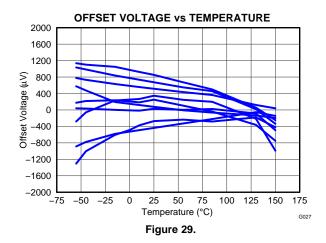


Figure 27.





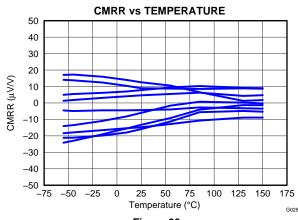


Figure 30.



At T_A = +25°C, R_L = 2 k Ω connected to ground, and V_S = ±15 V, unless otherwise noted.

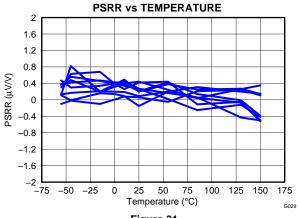


Figure 31.

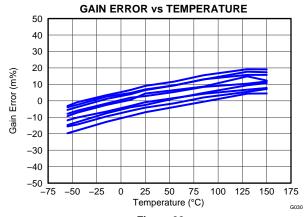


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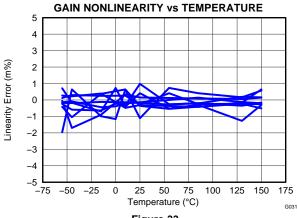
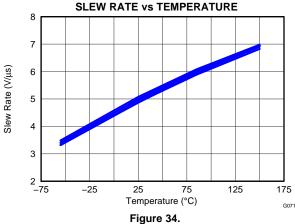


Figure 33.



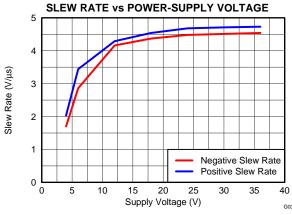


Figure 35.

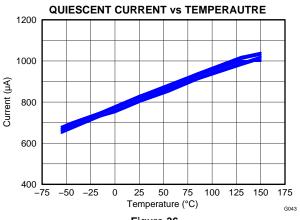


Figure 36.



At $T_A = +25$ °C, $R_L = 2 \text{ k}\Omega$ connected to ground, and $V_S = \pm 15 \text{ V}$, unless otherwise noted.

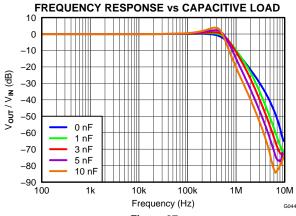


Figure 37.

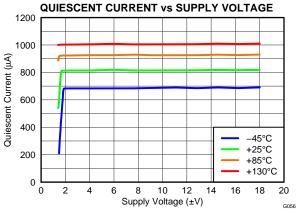


Figure 38.

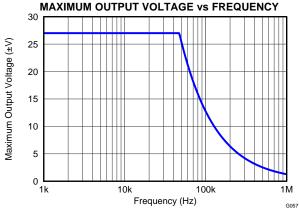


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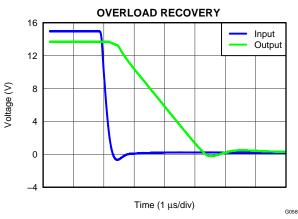


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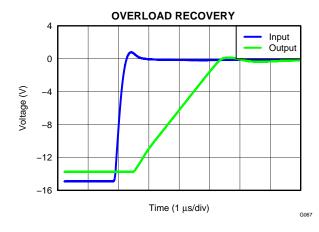


Figure 41.

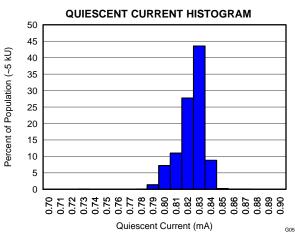


Figure 42.



APPLICATION INFORMATION

BASIC INFORMATION

Figure 43 shows the basic connections required for dual-supply operation. Applications with noisy or highimpedance power-supply lines may require decoupling capacitors placed close to the device pins. The output voltage is equal to the differential input voltage between pins 2 and 3. The common-mode input voltage is rejected. Figure 44 shows the basic connections required for single-supply operation.

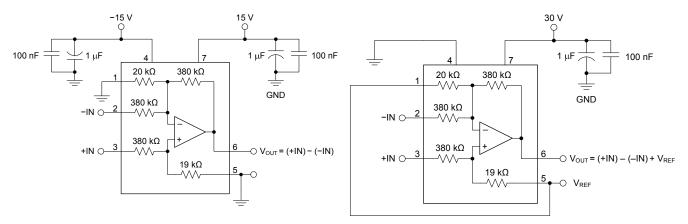


Figure 43. Basic Power and Signal Connections for Figure 44. Basic Power and Signal Connections for **Dual-Supply Operation**

Single-Supply Operation

TRANSFER FUNCTION

Most applications use the INA149 as a simple unity-gain difference amplifier. The transfer function is given in Equation 1:

$$V_{OUT} = (+IN) - (-IN) \tag{1}$$

Some applications, however, apply voltages to the reference terminals (REF_A and REF_B). The complete transfer function is given in Equation 2:

$$V_{OUT} = (+IN) - (-IN) + 20 \times REF_A - 19 \times REF_B$$
 (2)

COMMON-MODE RANGE

The high common-mode range of the INA149 is achieved by dividing down the input signal with a high precision resistor divider. This resistor divider brings both the positive input and the negative input within the input range of the internal operational amplifier. This input range depends on the supply voltage of the INA149.

Both Figure 2 and Figure 3 can be used to determine the maximum common-mode range for a specific supply voltage. The maximum common-mode range can also be calculated by ensuring that both the positive and the negative input of the internal amplifier are within 1.5 V of the supply voltage.

In case the voltage at the inputs of the internal amplifier exceeds the supply voltage, the internal ESD diodes start conducting current. This current must be limited to 10 mA to make sure not to exceed the absolute maximum ratings for the device.

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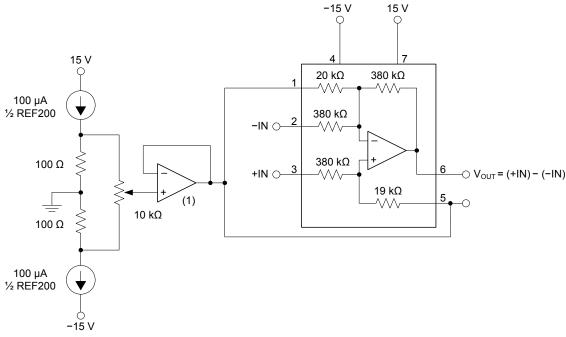


COMMON-MODE REJECTION

Common-mode rejection (CMR) of the INA149 depends on the input resistor network, which is laser-trimmed for accurate ratio matching. To maintain high CMR, it is important to have low source impedance driving the two inputs. A 75- Ω resistance in series with pins 2 or 3 decreases the common-mode rejection ratio (CMRR) from 100 dB (typical) to 74 dB.

Resistance in series with the reference pins also degrades CMR. A 4- Ω resistance in series with pins 1 or 5 decreases CMRR from 100 dB to 74 dB.

Most applications do not require trimming. Figure 45 shows an optional circuit that may be used for trimming offset voltage and common-mode rejection.



(1) The OPA171 (a 36-V, low-power, RRO, general-purpose operational amplifier) can be used for this application.

Figure 45. Offset Voltage Trim Circuit



MEASURING CURRENT

The INA149 can be used to measure a current by sensing the voltage drop across a series resistor, R_S. Figure 46 shows the INA149 used to measure the supply currents of a device under test.

The sense resistor imbalances the input resistor matching of the INA149, thus degrading its CMR. Also, the input impedance of the INA149 loads R_S, causing gain error in the voltage-to-current conversion. Both of these errors can be easily corrected.

The CMR error can be corrected with the addition of a compensation resistor (R_C), equal to the value of R_S , as shown in Figure 46. If R_S is less than 5 Ω , degradation in the CMR is negligible and R_C can be omitted. If R_S is larger than approximately 1 $k\Omega$, trimming R_C may be required to achive greater than 90-dB CMR. This error is caused by the INA149 input impedance mismatch.

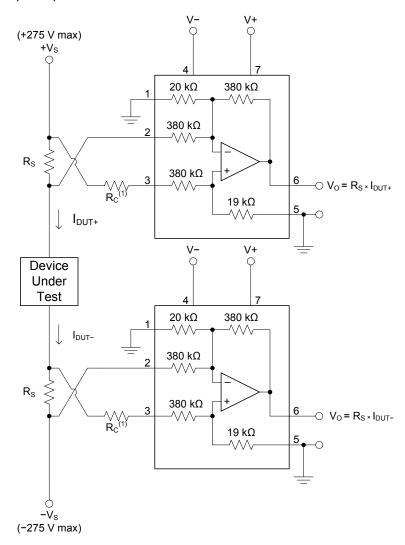


Figure 46. Measuring Supply Currents of a Device Under Test

If R_S is more than approximately 50 Ω , the gain error is greater than the 0.02% specification of the INA149. This gain error can be corrected by slightly increasing the value of R_S . The corrected value (R_S ') can be calculated by R_S ' = $R_S \times 380 \text{ k}\Omega/(380 \text{ k}\Omega - R_S)$

Example: For a 1-V/mA transfer function, the nominal, uncorrected value for R_S would be 1 k Ω . A slightly larger value ($R_S' = 1002.6 \Omega$), compensates for the gain error as a result of loading.

The 380-k Ω term in the equation for R_S' has a tolerance of 25%, thus sense resistors above approximately 400 Ω may require trimming to achive gain accuracy better than 0.02%.

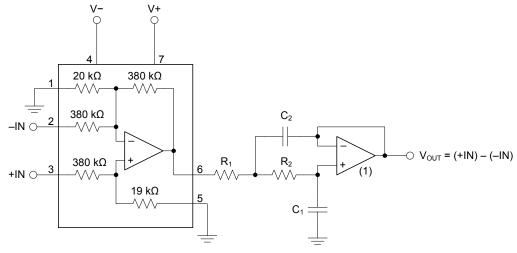


NOISE PERFORMANCE

The wideband noise performane of the INA149 is dominated by the internal resistor network. The thermal or *Johnson noise* of these resistors measures approximately 550 nV/ $\sqrt{\text{Hz}}$. The internal op amp contributes virtually no excess noise at frequencies above 100 Hz.

Many applications may be satisfied with less than the full 500-kHz bandwidth of the INA149. In these cases, the noise can be reduced with a low-pass filter on the output. The two-pole filter shown in Figure 47 limits bandwidth and reduces noise. Because the INA149 has a 1/f noise corner frequency of approximately 100 Hz, a cutoff frequency below 100 Hz does not further reduce noise.

Component values for different filter frequencies are shown in Table 1.



(1) For most applications, the OPA171 can be used as an operational amplifier. For directly driving successive-approximation register (SAR) data converters, the OPA140 is a good choice.

Figure 47. Output Filter for Noise Reduction

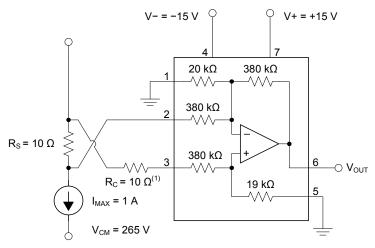
Table 1. Components Values for Different Filter Bandwidths

BUTTERWORTH LOW-PASS (f _{-3 dB})	OUTPUT NOISE (mV _{PP})	R ₁	R ₂	C ₁	C ₂		
200 kHz	1.8		No	filter			
100 kHz	1.1	11 kΩ	11.3 kΩ	100 pF	200 pF		
10 kHz	0.35	11 kΩ	11.3 kΩ	1 nF	2 nF		
1 kHz	0.11	11 kΩ	11.3 kΩ	10 nF	20 nF		
100 Hz	0.05	11 kΩ	11.3 kΩ	0.1 μF	0.2 μF		



ERROR BUDGET ANALYSIS

The following error budget analysis demonstrates the importance of a high common-mode rejection ratio when measuring small differential signals in the presence of high common-mode voltages. Figure 48 shows a typical current measurement application.



(1) See the *Measuring Current* section for details about R_C.

Figure 48. Typical Current Measurement Application

The maximum current through the shunt resistor (R_S) is 1 A and generates a full-scale voltage drop of 10 V. All error sources in this calculation are shown in relation to this full-scale voltage. The common-mode voltage in this scenario is 265 V and the temperature range is from room temperature (+25°C) to +85°C. Table 2 shows the dominant error sources for the INA149 and a competitor device.

ERROR (ppm of FS) **ERROR SOURCE INA149 COMPETIOR A INA149 COMPETITOR A** Accuracy, $T_A = +25$ °C Initial gain error 0.02% FS 0.05% FS 200 500 Offset voltage 1100 µV 1000 μV 110 100 Common mode $265 \text{ V/90 dB} = 8380 \,\mu\text{V}$ $265 \text{ V/77 dB} = 37432 \,\mu\text{V}$ 838 3743 Total acuracy error 1148 4343 Temperature drift 10 ppm/°C \times 60°C 10 ppm/°C \times 60°C Gain 600 600 $10 \mu V/^{\circ}C \times 60^{\circ}C$ 20 μV/°C × 60°C Offset voltage 60 120 Total drift error 660 720 **Total error** 1808 5063

Table 2. Error Budget Analysis

If a smaller shunt resistor is used, the full-scale voltage drop is also smaller. A shunt resistor of 1 Ω causes a 1-V voltage drop with a current of 1 A flowing through it. The error of 1808 ppm for a full-scale voltage of 10 V becomes 18080 ppm (1.6%) for a full-scale voltage of only 1 V.

This example demonstrates that the dominate source of error, even over temperature, comes from the CMRR specification of the devices. The common-mode error is 46% of the total error for the INA149 and 74% of the total error for the competitor device.



BATTERY CELL VOLTAGE MONITOR

The INA149 can be used to measure the voltages of single cells in a stacked battery pack. Figure 49 shows an examples for such an application.

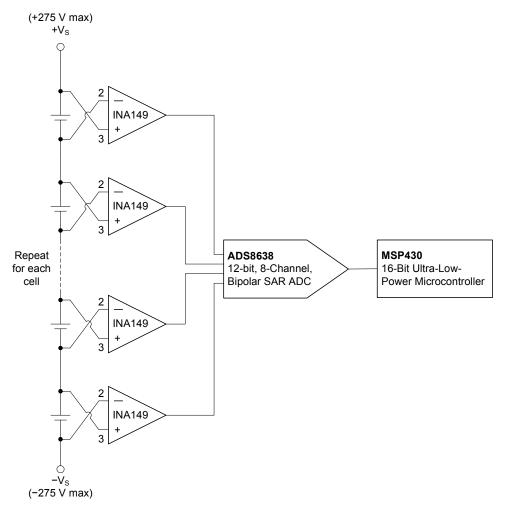


Figure 49. Battery Cell Voltage Monitor

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REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	hanges from Revision A (November 2011) to Revision B	Page
•	Changed package marking data in Package/Ordering Information table	

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
INA149AID	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 149A
INA149AID.B	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 149A
INA149AIDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 149A
INA149AIDR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 149A
INA149AIDRG4.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 149A

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF INA149:

● Enhanced Product : INA149-EP

NOTE: Qualified Version Definitions:

• Enhanced Product - Supports Defense, Aerospace and Medical Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	_	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA149AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA149AIDR	SOIC	D	8	2500	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
INA149AID	D	SOIC	8	75	506.6	8	3940	4.32
INA149AID.B	D	SOIC	8	75	506.6	8	3940	4.32



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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